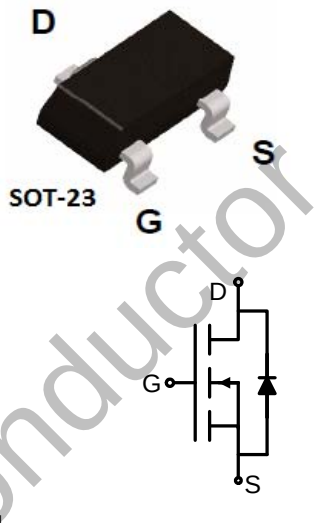
WG3404

30V N-Channel MOSFET

Features:

- ☐ Low Intrinsic Capacitances.
- ☐ Excellent Switching Characteristics.
- ☐ Extended Safe Operating Area.
- ☐ Unrivalled Gate Charge :Qg= 5.2nC (Typ.).
- ☐ BVDSS=30V,I_D=5.8A
- ☐ R_{DS}(on) : 31mΩ (Max) @V_G=10V
- ☐ 100% Avalanche Tested

SOT-23



MARKING:**3404**

Schematic diagram

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Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	5.8	A
Drain Current-Pulsed (Note 1)	I_{DM}	20	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	89	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	30	33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.2	1.6	2.4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=5A	-	25.5	31	mΩ
		V_{GS}=4.5V, I_D=4A	-	36	43	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=5A	-	15	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=15V,V_{GS}=0V, F=1.0MHz	-	255	-	PF
Output Capacitance	C_{oss}		-	45	-	PF
Reverse Transfer Capacitance	C_{rss}		-	35	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=15V, R_L=3Ω V_{GS}=10V,R_{GEN}=3Ω	-	4.5	-	nS
Turn-on Rise Time	t_r		-	2.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	14.5	-	nS
Turn-Off Fall Time	t_f		-	3.5	-	nS
Total Gate Charge	Q_g	V_{DS}=15V,I_D=5A, V_{GS}=10V	-	5.2	-	nC
Gate-Source Charge	Q_{gs}		-	0.85	-	nC
Gate-Drain Charge	Q_{gd}		-	1.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=5A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	5	A

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Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Characteristics

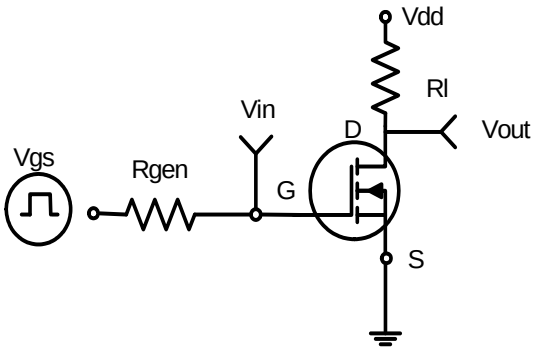


Figure 1:Switching Test Circuit

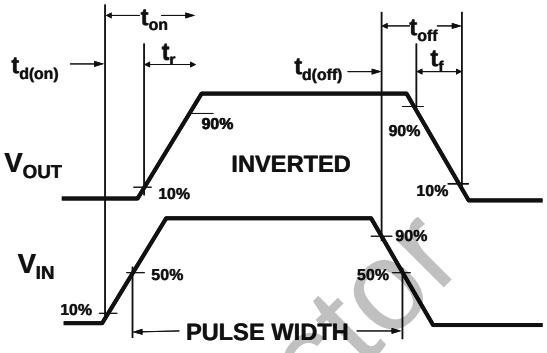


Figure 2:Switching Waveforms

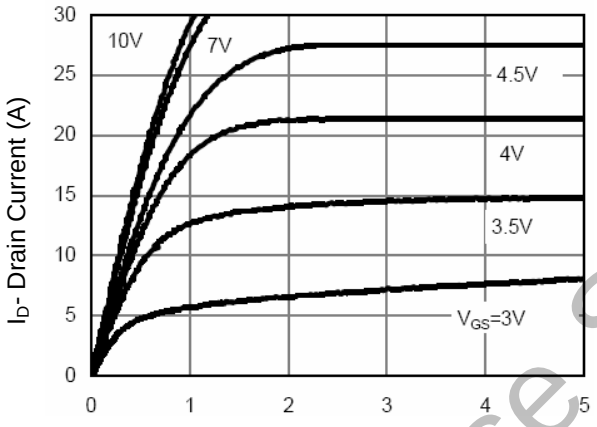


Figure 3 Output Characteristics

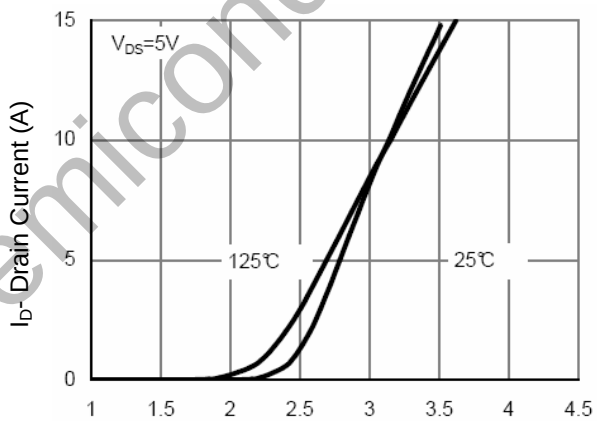


Figure 4 Transfer Characteristics

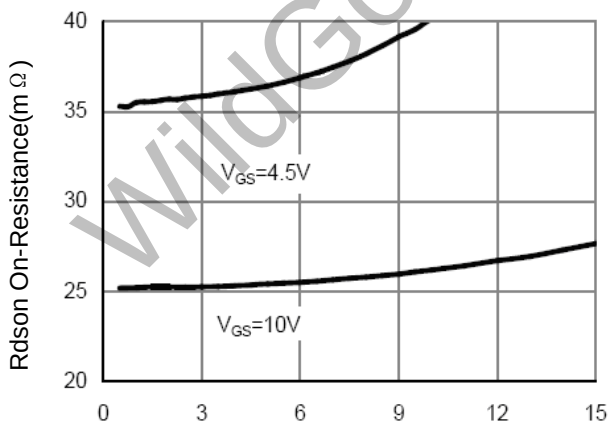


Figure 5 Drain-Source On-Resistance

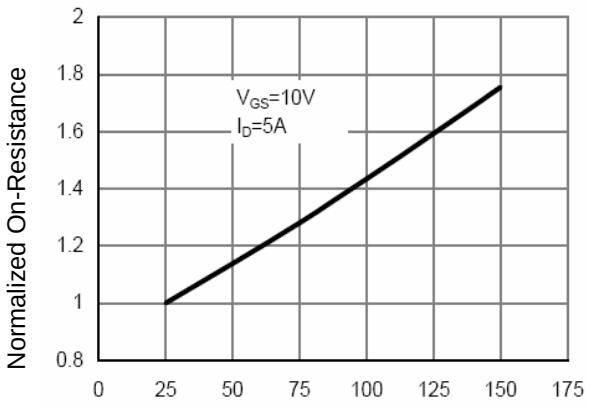


Figure 6 Drain-Source On-Resistance

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Typical Characteristics (Continued)

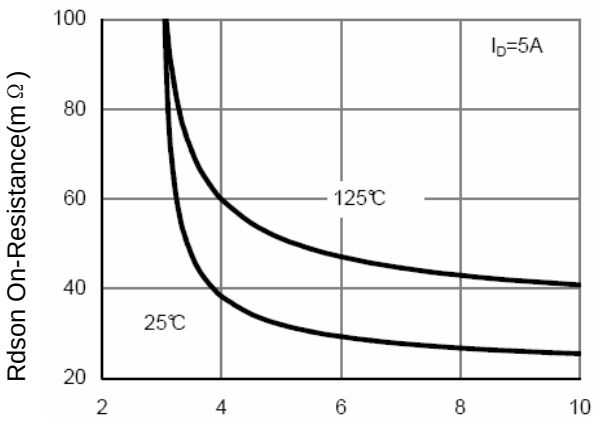


Figure7 Rdson vs Vgs

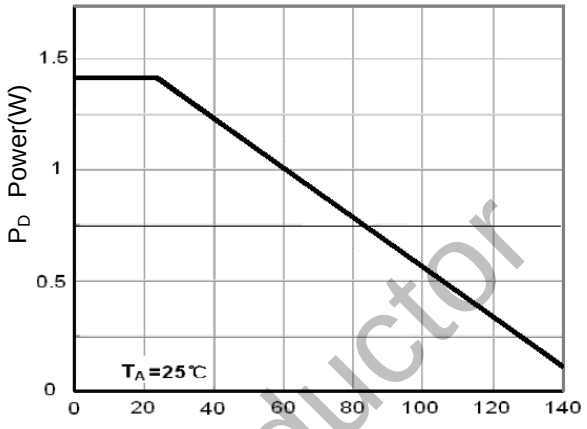


Figure 8 Power Dissipation

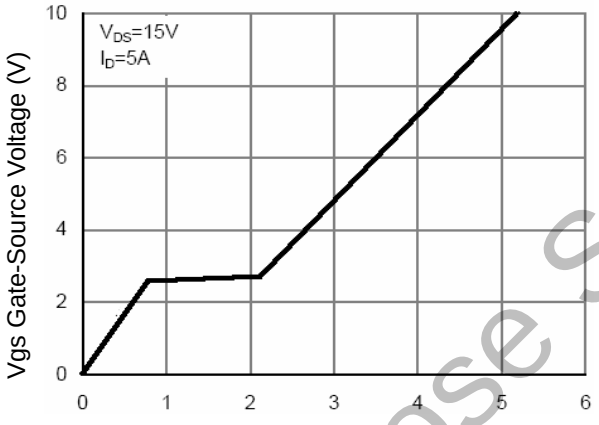


Figure 9 Gate Charge

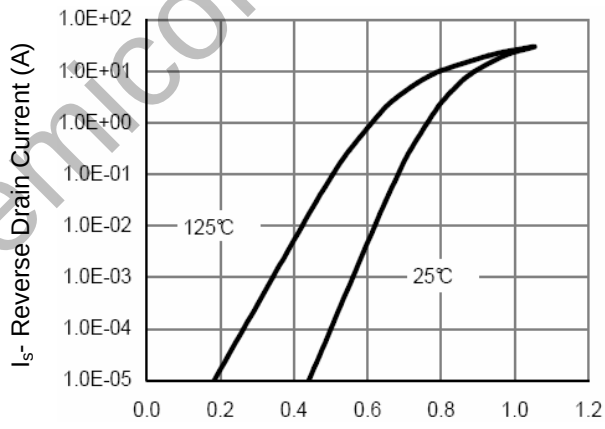


Figure 10 Source- Drain Diode Forward

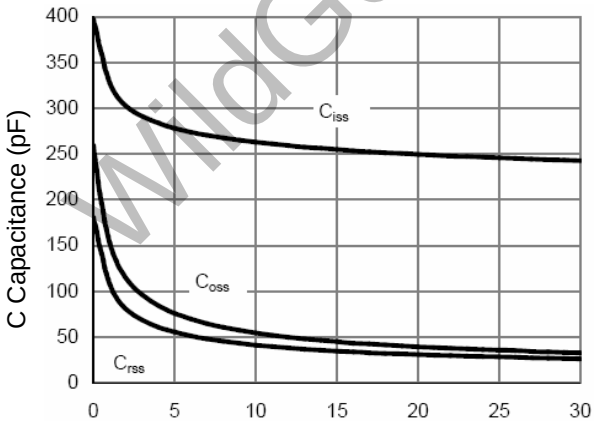


Figure 11 Capacitance vs Vds

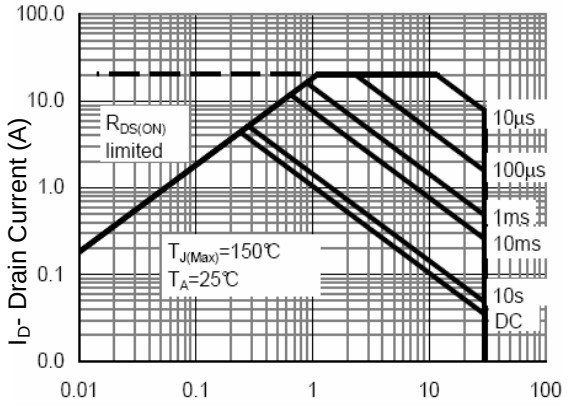


Figure 12 Safe Operation Area

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Typical Characteristics (Continued)

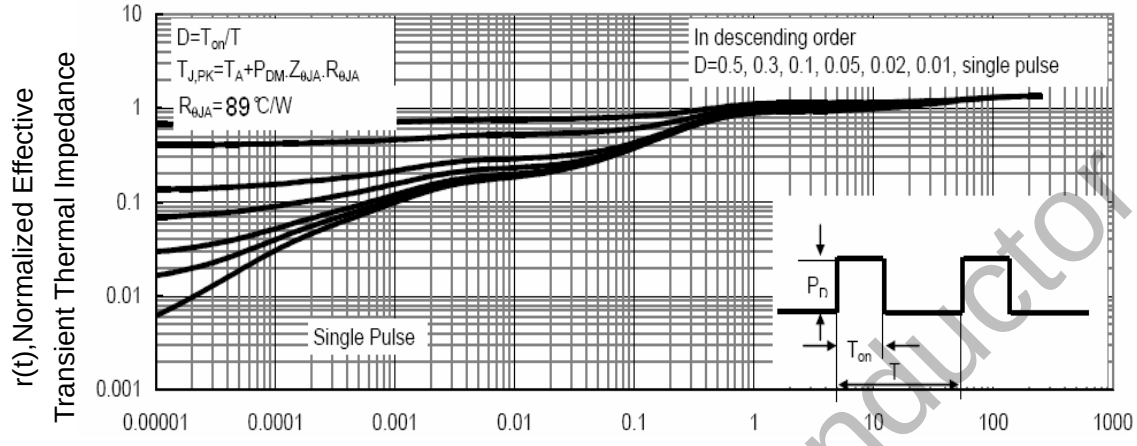


Figure 13 Normalized Maximum Transient Thermal Impedance

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